

UNITED STATES PATENT AND TRADEMARK OFFICE





UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER OF PATENTS AND TRADEMARKS Washington, D.C. 20231 www.uspto.gov

			······································	
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/660,884	09/12/2000	Takashi Akahori	08038.0038	7052
759	01,1,7,2002			
Finnegan Henderson Farabow Garrett & Dunner LLP 1300 I Street NW			EXAMINER	
Washington, DC 20005-3315			WILLIAMS, ALEXANDER O	
			ART UNIT	PAPER NUMBER
			2826	7
	1			
				•

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	
		Application No.	blicant(s)
	Office Action Summan	09/660,884	AKAHORI ET AL.
	Office Action Summary	Examiner	Art Unit
	The ARAH Was DATE and	Alexander O Williams	2826
Period fo	The MAILING DATE of this communication app or Reply	ears on the cover sheet with a	the correspondence address
I HE - Exte. after - If the - If NC - Failu - Any r earne	ORTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. Insions of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. In period for reply specified above is less than thirty (30) days, a reply operiod for reply is specified above, the maximum statutory period we are to reply within the set or extended period for reply will, by statute, reply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply within the statutory minimum of thirty (30 will apply and will expire SIX (6) MONTHS	be timely filed 2) days will be considered timely. 3) from the mailing date of this communication.
Status	_		
1) 🖂	Responsive to communication(s) filed on	·-	
2a) ☐		s action is non-final.	
3) 🗌	Since this application is in condition for allowa closed in accordance with the practice under the conditions of the condition of the conditio	nce except for formal matters Ex parte Quayle, 1935 C.D. 1	s, prosecution as to the merits is 1, 453 O.G. 213.
Dispositi	on of Claims		
4) 🖾	Claim(s) <u>1-9</u> is/are pending in the application.		
	4a) Of the above claim(s) is/are withdraw	n from consideration.	
5)	Claim(s) is/are allowed.		
6)🖂	Claim(s) <u>1-9</u> is/are rejected.		
7)	Claim(s) is/are objected to.		
8) 🗌	Claim(s) are subject to restriction and/or	election requirement.	
	on Papers		
9)□ T	The specification is objected to by the Examiner		
10) 🔲 T	he drawing(s) filed on is/are: a) accept	ed or b) objected to by the E	Examiner.
	Applicant may not request that any objection to the		
11) 🔲 T	he proposed drawing correction filed on	is: a) approved b) disap	proved by the Examiner.
	If approved, corrected drawings are required in repl		•
12) 🗌 T	he oath or declaration is objected to by the Exa	miner.	
riority u	nder 35 U.S.C. §§ 119 and 120		
13) 🛛 🗸	Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 11	9(a)-(d) or (f).
	☑ All b) ☐ Some * c) ☐ None of:	•	
•	1. Certified copies of the priority documents	have been received.	
	2. Certified copies of the priority documents		cation No.
	3. Copies of the certified copies of the priorit application from the International Bure se the attached detailed Office action for a list of	y documents have been rece au (PCT Rule 17.2(a))	eived in this National Stage
	cknowledgment is made of a claim for domestic		
a)	☐ The translation of the foreign language provi	isional application has been i	received.
15)∐ Ad	cknowledgment is made of a claim for domestic	priority under 35 U.S.C. §§ 1	20 and/or 121.
tachment(s	•		
☐ Notice	of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (PTO-948) ation Disclosure Statement(s) (PTO-1449) Paper No(s) <u>5</u> .		nary (PTO-413) Paper No(s) al Patent Application (PTO-152)
Patent and Trad O-326 (Rev.		on Summary	Part of Paper No. 7





Art Unit: 2826

Serial Number: 09/660884 Attorney's Docket #: 08038.0025

Filing Date: 9/12/00; claimed foreign priority to 5/7/98

Applicant: Akahori et al.

Examiner: Alexander Williams

Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

The following is a quotation of the appropriate paragraphs of 35 U.S.C. § 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains.

Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of



Art Unit: 2826

the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(f) or (g) prior art under 35 U.S.C. 103(a).

Claims 1, 2 and 5 are rejected under 35 U.S.C. § 102(b) as being anticipated by (Japan Patent Application # 9-246242).

For example, in claim 1, (Japan Patent Application # 9-246242) (figures 1 to 11) specifically figure 7 show a semiconductor device comprising: a substrate **21**; an insulating film **2312** of a fluorine-containing carbon film formed on said substrate; and a wiring layer **261** of copper formed on said insulating film.

For example, in claim 2, (Japan Patent Application # 9-246242) (figures 1 to 11) specifically figure 7 show a semiconductor device comprising: a substrate 21; an insulating film 2312 of a fluorine-containing carbon film formed on said substrate; a wiring layer 261 of copper formed on said insulating film; an adhesion layer 251 formed between said insulating film and said wiring layer, for preventing said wiring layer from being peeled off from said insulating film.

Claims 1, 2 and 5 are rejected under 35 U.S.C. § 102(b) as being anticipated by (Japan Patent Application # 9-246264).

For example, in claim 1, (Japan Patent Application # 9-246264) (figures 1 to 3) specifically figure 1 show a semiconductor device **10** comprising: a substrate **12**; an insulating film **18** of a fluorine-containing carbon film formed on said substrate; and a wiring layer **16** of copper formed on said insulating film.

For example, in claim 2, (Japan Patent Application # 9-246264) (figures 1 to 3) specifically figure 3 show a semiconductor device **50** comprising: a substrate **52**; an insulating film **58** of a fluorine-containing carbon film formed on said substrate; a wiring layer **54** of copper formed on said insulating film; an adhesion layer **60** formed between said insulating film and said wiring layer, for preventing said wiring layer from being peeled off from said insulating film.



Art Unit: 2826

Claims 1 to 9 are rejected under 35 U.S.C. § 102(e) as being anticipated by Matsubara et al. (U.S. Patent # 6,091,081).

For example, in claim 1, Matsubara (figures 1 to 25) specifically figure 12 show a semiconductor device comprising: a substrate 1; an insulating film of a fluorine-containing carbon film 43 formed on said substrate; and a wiring layer of copper 8 formed on said insulating film.

For example, in claim 2, Matsubara (figures 1 to 25) specifically figure 12 show a semiconductor device comprising: a substrate 1; an insulating film of a fluorine-containing carbon 43 film formed on said substrate; a wiring layer of copper 8 formed on said insulating film; an adhesion layer 44, formed between said insulating film and said wiring layer, for preventing said wiring layer from being peeled off from said insulating film.

As to claims 6 to 9, Note that the specification contains no disclosure of either the critical nature of the claimed dimensions or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimensions or upon another variable recited in a claim, the Applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).

Claims 1 to 9 are rejected under 35 U.S.C. § 102(e) as being anticipated by Matsumoto et al. (U.S. Patent # 5,866,920).

For example, in claim 1, Matsumoto et al. (figures 1 to 7 to 8h) specifically figure 7 show a semiconductor device comprising: a substrate 21, an insulating film of a fluorine-containing carbon film 231 formed on said substrate; and a wiring layer of copper 271 formed on said insulating film.

For example, in claim 2, Matsumoto et al. (figures 1 to 7 to 8h) specifically figure 7 show a semiconductor device comprising: a substrate 21; an insulating film of a fluorine-containing carbon 231 film formed on said substrate; a wiring layer of copper 271 formed on said insulating film; an adhesion layer 241, formed between said insulating film and said wiring layer, for preventing said wiring layer from being peeled off from said insulating film.

As to claims 6 to 9, Note that the specification contains no disclosure of either the critical nature of the claimed dimensions or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimensions or upon another variable recited in a claim, the Applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).



Art Unit: 2826

Claims 3, 4 and 6 to 9 are rejected under 35 U.S.C. § 103(a) as being unpatentable over (Japan Patent Application # 9-246242).

Note that the specification contains no disclosure of either the critical nature of the claimed dimensions or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimensions or upon another variable recited in a claim, the Applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).

Claims 3 and 4 are rejected under 35 U.S.C. § 103(a) as being unpatentable over (Japan Patent Application # 9-246264) in view of Hoshino (U.S. Patent # 4,985,750).

(Japan Patent Application # 9-246264) show the features of the claimed invention as detailed above, but fail to explicitly show an adhesion layer comprising a metal layer of a metal and a layer of a compound containing carbon and said metal and the metal being titanium.

Hoshino is cited for showing a semiconductor device using copper metallization. Specifically, Hoshino discloses (figures 2) discloses an adhesion layer **18a** comprising a metal layer of a metal and a layer of a compound containing carbon and said metal and the metal being titanium for the purpose of provide a semiconductor device, in which a leakage current which flows from a diffused layer formed in a silicon substrate is limited.

Therefore, it would have been obvious to one of ordinary skill in the art to use Hoshino's metal to modify (Japan Patent Application # 9-246264)'s metal for the purpose of provide a semiconductor device, in which a leakage current which flows from a diffused layer formed in a silicon substrate is limited.

Claims 6 to 9 are rejected under 35 U.S.C. § 103(a) as being unpatentable over (Japan Patent Application # 9-246264).

Note that the specification contains no disclosure of either the critical nature of the claimed dimensions or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimensions or upon another variable recited in a claim, the Applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990)

The listed references are cited as of interest to this application, but not applied at this time.



Art Unit: 2826

Field of Search	Date
U.S. Class and subclass: 257/762,758,700,701,774,751,759,760,763,764,767,773	1/12/02
Other Documentation: foreign patents and literature in 257/762,758,700,701,774,751,759,760,763,764,767,773 Electronic data base(s):	1/12/02
U.S. Patents EAST	1/12/02

Papers related to this application may be submitted to Technology Center 2800 by facsimile transmission. Papers should be faxed to Technology Center 2800 via the Technology Center 2800 Fax center located in Crystal Plaza 4-5B15. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (November 15, 1989). The Technology Center 2800 Fax Center number is (703) 308-7722 or 24. Only Papers related to Technology Center 2800 APPLICATIONS SHOULD BE FAXED to the GROUP 2800 FAX CENTER.

Any inquiry concerning this communication or any earlier communication from the examiner should be directed to *Examiner Alexander Williams* whose telephone number is **(703) 308-4863**.

Any inquiry of a general nature or relating to the status of this application should be directed to the *Technology Center 2800* receptionist whose telephone number is (703) 308-0956.

1/13/02

Primary Examiner Alexander O. Williams